MBRF20H100CT

Rev.F Mar.-2016

DATA SHEET

/ Descriptions

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Schottky Barrier Diode in a TO-220F Plastic Package.

/ Features

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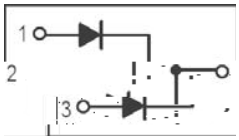
Low power loss,high efficiency.

/ Applications

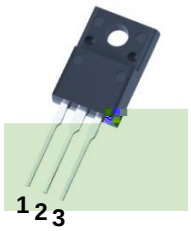
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For use in low voltage,high frequency inverters, free wheeling, and polarity protection applications.

/ Equivalent Circuit



/ Pinning



PIN1 χ Anode PIN 2 χ Cathode PIN 3 χ Anode

/ h_{FE} Classifications & Marking

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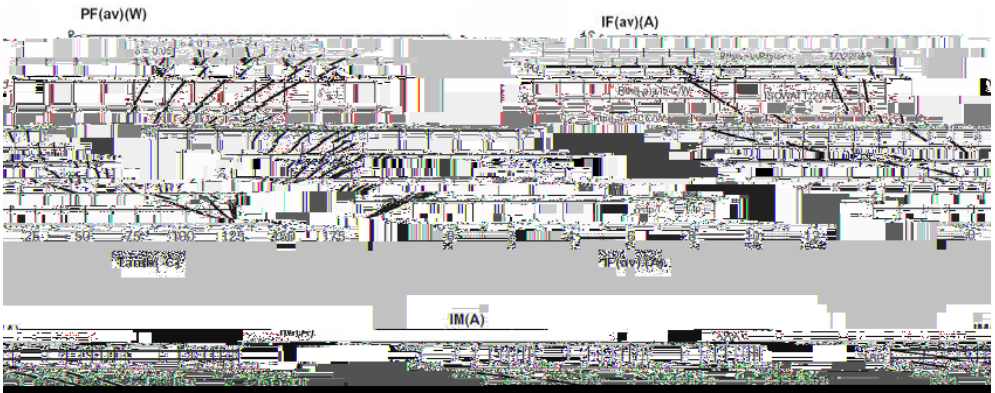
/ Absolute Maximum Ratings(Ta=25)

v ̈Ω Parameter	ϒ N Symbol	̈Ω Ö Rating	D Ч Unit
Peak Repetitive Reverse Voltage	V_{RRM}	100	V
Average Rectified Forward Current	I_F	30	A
Average Forward Current	$I_{F(AV)}$	10	A
Average Forward Current Total	$I_{F(AV)}$ total device	20	A
Non Repetitive Peak Surge Current	I_{FSM}	250	A
Repetitive peak reverse current	I_{RRM}	1.0	A
Non repetitive peak reverse current	I_{RSM}	3.0	A
Thermal Resistance, Junction to Case	R_{JC}	1.6	/W
Junction 6nmperature Range	$T_{j,}$	175	
Storage 6nmperature Range	T_{stg}	-55~175	

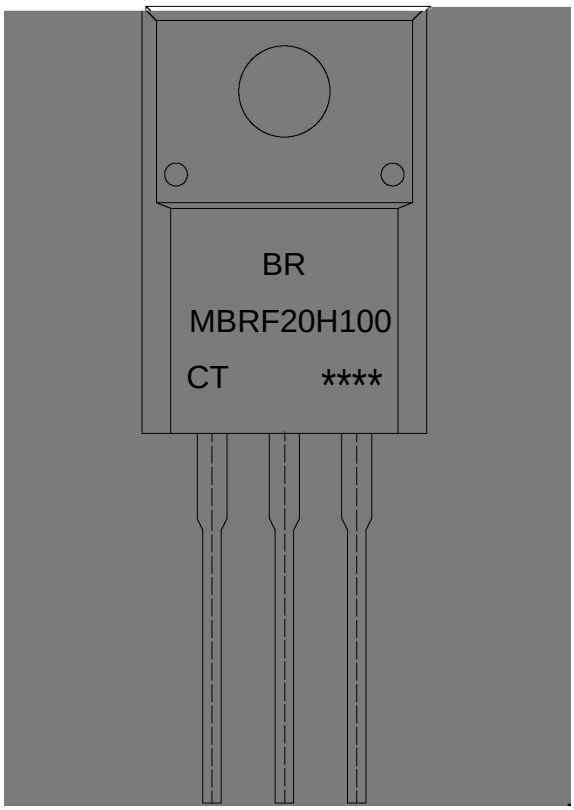
/ Electrical Characteristics(Ta=25)

v ̈Ω Parameter	ϒ N Symbol	Ш ;ϯ Ţ Test Conditions	ϣ ņ Ö Min	Ɛ ʒ Ö Typ	ϣ ƶ Ö Max	D Ч Unit
Forward Voltage	V_F	I_F =8A(Tc=25)			0.71	V
		I_F =8A(Tc=125)		0.56	0.58	V
		I_F =10A(Tc=25)			0.77	V
		I_F =10A(Tc=125)		0.59	0.64	V
		I_F =16A(Tc=25)			0.81	V
		I_F =16A(Tc=125)		0.65	0.68	V
		I_F =20A(Tc=25)			0.88	V
		I_F =20A(Tc=125)		0.67	0.73	V
Instantaneous Reverse Current	I_R	V_R =100V(Tc=25)			100	uA
		V_R =100V(Tc=125)			6.0	mA
Voltage Rate of Change	dv/dt				10000	V/ s

/ Electrical Characteristic Curve



/ Marking Instructions



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Note:

BR:	Company Code
MBRF20H100:	Product Type.
CT:	Internal Structure
****:	Lot No. Code, code change with Lot No.

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